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January 2014

# FDD1600N10ALZ

# N-Channel PowerTrench® MOSFET 100 V, 6.8 A, 160 m $\Omega$

#### **Features**

- $R_{DS(on)}$  = 124 m $\Omega$  (Typ.) @  $V_{GS}$  = 10 V,  $I_D$  = 3.4 A
- $R_{DS(on)} = 175 \text{ m}\Omega \text{ (Typ.)} @ V_{GS} = 5 \text{ V, } I_D = 2.1 \text{ A}$
- Low Gate Charge (Typ.2.78 nC)
- Low C<sub>rss</sub> (Typ. 2.04 pF)
- · Fast Switching
- · 100% Avalanche Tested
- · Improved dv/dt Capability
- · RoHS Compliant

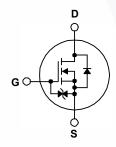
# **Description**

This N-Channel MOSFET is produced using Fairchld Semiconductor's advanced PowerTrench® process that has been tailored to minimize the on-state resistance and maintain superior switching performance.

#### **Application**

- · Consumer Appliances
- · LED TV and Monitor
- · Synchronous Rectification
- Uninterruptible Power Supply
- · Micro Solar Inverter





## MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter			FDD1600N10ALZ	Unit
V <sub>DSS</sub>	Drain to Source Voltage			100	V
V <sub>GSS</sub>	Gate to Source Voltage			±20	V
	Drain Current	- Continuous (T <sub>C</sub> = 25°C	5)	6.8	А
ID	Drain Current  - Continuous (T <sub>C</sub> = 100°C)		4.3	A	
I <sub>DM</sub>	Drain Current	- Pulsed	- Pulsed (Note 1)		Α
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)			5.08	mJ
dv/dt	Peak Diode Recovery dv/	dt	(Note 3)	6.0	V/ns
D	Dower Dissipation	(T <sub>C</sub> = 25°C)		14.9	W
$P_{D}$	Power Dissipation	- Derate Above 25°C		0.12	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temperat	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			°C

#### **Thermal Characteristics**

Symbol	Parameter	FDD1600N10ALZ	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	8.4	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	87	30/44

©2012 Fairchild Semiconductor Corporation FDD1600N10ALZ Rev. C3

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDD1600N10ALZ	1600N10ALZ	DPAK	Tape and Reel	330 mm	16 mm	2500 units

# **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	100	-	-	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C	-	0.1	-	V/°C
1	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V	-	-	1	
IDSS Zero Gate voltage Drain Current	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	500	μА	
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±10	μА

#### On Characteristics

V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	1.4	-	2.8	V
P	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 3.4 \text{ A}$	-	124	160	mΩ
R <sub>DS(on)</sub>	NDS(on) Static Drain to Source On Resistance	V <sub>GS</sub> = 5 V, I <sub>D</sub> = 2.1 A	-	175	375	11122
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 6.8 A	-	19.6	-	S

#### **Dynamic Characteristics**

•							
C <sub>iss</sub>	Input Capacitance	V - 50 V V	- 0 ) /	-	169	225	pF
Coss	Output Capacitance	$V_{DS} = 50 \text{ V}, V_{GS}$ f = 1 MHz	= U V,	-\	43	55	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 1 1/11 12		- \	2.04	-	pF
C <sub>oss(er)</sub>	Energy Related Output Capacitance	$V_{DS}$ = 50 V, $V_{GS}$	= 0 V	1	85	-	pF
Q <sub>g(tot)</sub>	Total Gate Charge at 10V	V <sub>GS</sub> = 10 V	V <sub>DD</sub> = 50 V,	-	2.78	3.61	nC
Q <sub>g(tot)</sub>	Total Gate Charge at 5V	V <sub>GS</sub> = 5 V	I <sub>D</sub> = 6.8 A		1.5	1.95	nC
Q <sub>gs</sub>	Gate to Source Gate Charge			-	0.72	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge			-	0.56	-	nC
V <sub>plateau</sub>	Gate Plateau Volatge		(Note 4)	-	4.02	-	V
Q <sub>sync</sub>	Total Gate Charge Sync.	$V_{DS} = 0 \text{ V}, I_{D} = 3$	.4 A	- /	2.5	-	nC
Q <sub>oss</sub>	Output Charge	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 0 V		- /	5.2	-	nC
ESR	Equivalent Series Resistance (G-S)	f = 1 MHz		-/	2.1	-	Ω

#### **Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time		-	7	24	ns
t <sub>r</sub>		$V_{DD} = 50 \text{ V}, I_{D} = 6.8 \text{ A},$	-	2	14	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS} = 10 \text{ V}, R_G = 4.7 \Omega$	-	13	36	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4	-	2	14	ns

#### **Drain-Source Diode Characteristics**

I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		-		6.8	Α
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	13.6	Α
$V_{SD}$	Drain to Source Diode Forward Voltage V <sub>GS</sub> =	0 V, I <sub>SD</sub> = 6.8 A	-	-	1.3	V
t <sub>rr</sub>	Reverse Recovery Time V <sub>GS</sub> =	0 V, I <sub>SD</sub> = 6.8 A, V <sub>DS</sub> = 50 V,	-	37	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge dI <sub>F</sub> /dt =	= 100 A/μs	-	42	-	nC

#### Notes:

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 1 mH,  $I_{AS}$  =3.18 A,  $R_G$  = 25  $\Omega$ , starting  $T_J$  = 25°C.
- 3.  $I_{SD} \le 6.8$  A, di/dt  $\le 200$  A/ $\mu$ s,  $V_{DD} \le BV_{DSS}$ , starting  $T_J$  = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

### **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

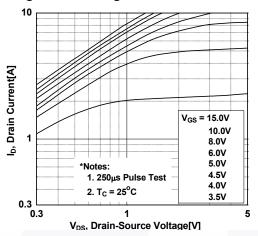


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

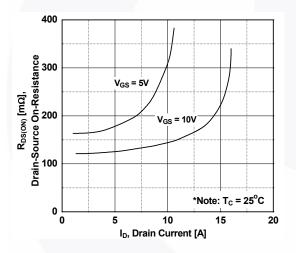


Figure 5. Capacitance Characteristics

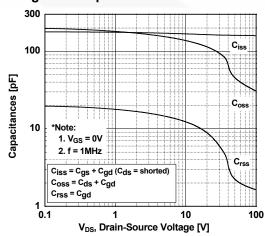


Figure 2. Transfer Characteristics

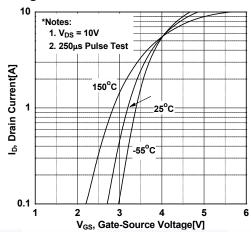


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

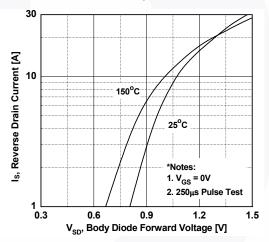
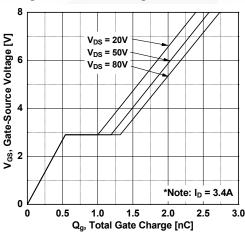


Figure 6. Gate Charge Characteristics



### **Typical Performance Characteristics** (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

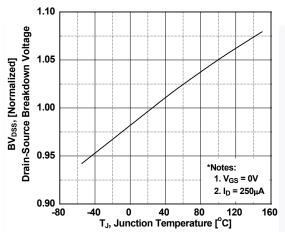


Figure 9. Maximum Safe Operating Area

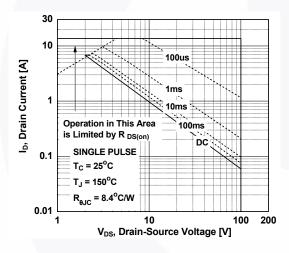


Figure 11. Eoss vs. Drain to Source Voltage

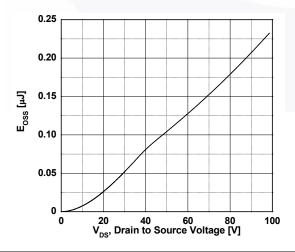


Figure 8. On-Resistance Variation vs. Temperature

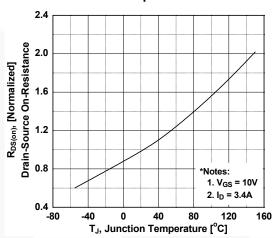


Figure 10. Maximum Drain Current vs. Case Temperature

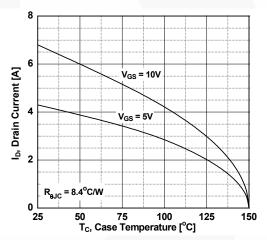
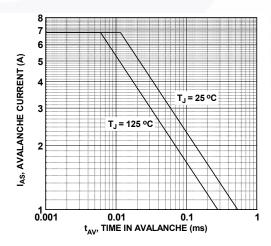


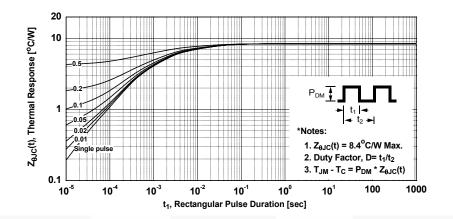
Figure 12. Unclamped Inductive Switching Capability



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# **Typical Performance Characteristics** (Continued)

Figure 13. Transient Thermal Response Curve



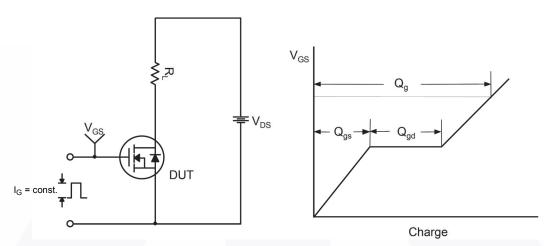


Figure 14. Gate Charge Test Circuit & Waveform

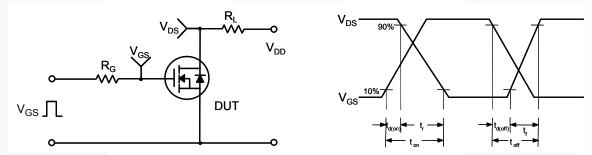


Figure 15. Resistive Switching Test Circuit & Waveforms

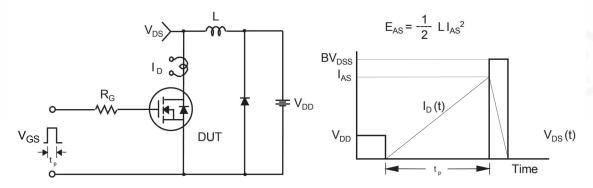


Figure 16. Unclamped Inductive Switching Test Circuit & Waveforms

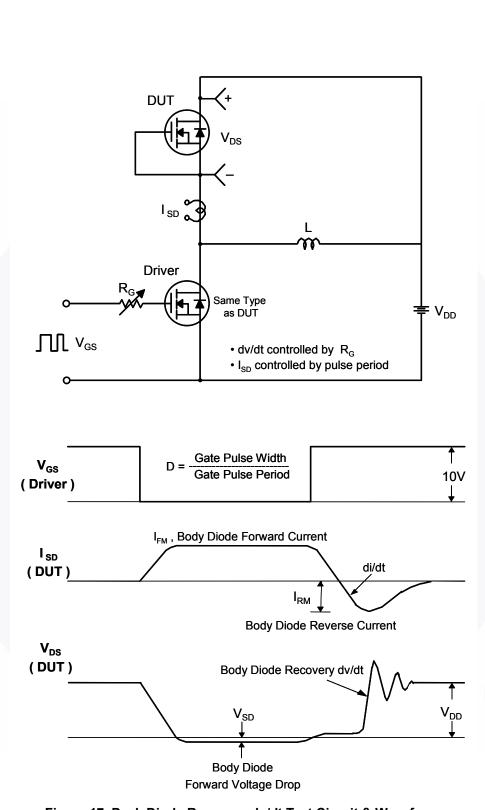


Figure 17. Peak Diode Recovery dv/dt Test Circuit & Waveforms

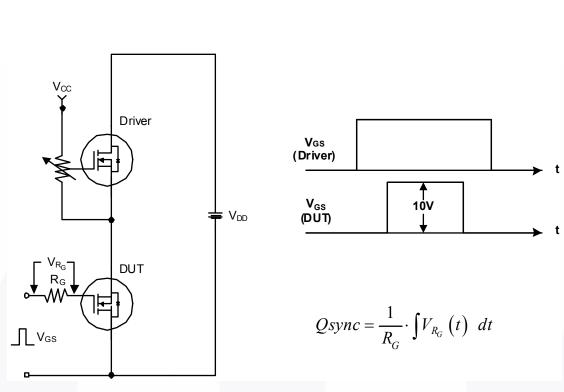


Figure 18. Total Gate Charge Qsync. Test Circuit & Waveforms

#### **Mechanical Dimensions** -5.55 MIN-1.27 6.22 6.50 MIN 1.02 MAX C 2 (0.59)0.89 2.29 ⊕ 0.25 A A C 4.57 LAND PATTERN RECOMMENDATION SFF 2.18 4.32 MIN NOTE D 0.58 0.45 5.21 MIN 10.41 9.40 SFF DFTAIL A ○ 0.10 B 0.51 GAGE PLANE NOTES: UNLESS OTHERWISE SPECIFIED THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA. ALL DIMENSIONS ARE IN MILLIMETERS. 10 (1.54)DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009. SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EGGE PROTRUSION. PRESENCE OF TRIMMED CENTER LEAD IS OPTIONAL. .78 .40 0.127 MAX DIMENSIONS ARE EXCLUSSIVE OF BURSS, MOLD FLASH AND TIE BAR EXTRUSIONS. SEATING PLANE (2.90)LAND PATTERN RECOMENDATION IS BASED ON IPC7351A STD DETAIL TO228P991X239-3N. (ROTATED -90°) SCALE: 12X DRAWING NUMBER AND REVISION: MKT-T0252A03REV9. FAIRCHILD SEMICONDUCTOR.

Figure 19. TO252 (D-PAK), Molded, 3-Lead, Option AA&AB

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